

# N-channel TrenchMOS SiliconMAX standard level FET Rev. 02 — 4 January 2011 Product de

Product data sheet

#### **Product profile** 1.

### 1.1 General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

### 1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- **1.3 Applications** 
  - DC-to-DC converters

- Suitable for high frequency applications due to fast switching characteristics
- Switched-mode power supplies

### 1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	200	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C	-	-	39	А
P <sub>tot</sub>	total power dissipation		-	-	250	W
Static cha	aracteristics					
$R_{DSon}$	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 17 A; T <sub>j</sub> = 25 °C	-	41	57	mΩ
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 39 A; V <sub>DS</sub> = 160 V; T <sub>j</sub> = 25 °C	-	37	50	nC



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### 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

### 3. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN057-200P	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

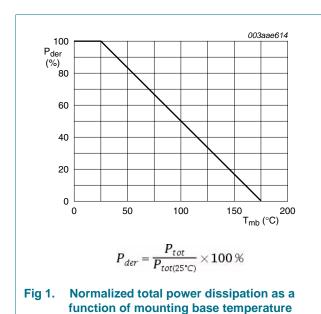
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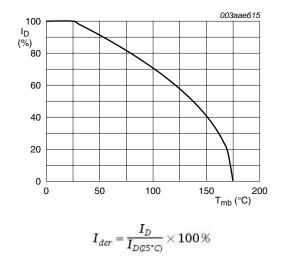
### 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	200	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	200	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 100 °C	-	27.5	А
		T <sub>mb</sub> = 25 °C	-	39	А
I <sub>DM</sub>	peak drain current	pulsed; T <sub>mb</sub> = 25 °C	-	156	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-	250	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
ls	source current	T <sub>mb</sub> = 25 °C	-	39	А
I <sub>SM</sub>	peak source current	pulsed; T <sub>mb</sub> = 25 °C	-	156	А
Avalanche rug	ggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$      V_{GS} = 10 \text{ V};  \text{T}_{j(init)} = 25 \text{ °C};  \text{I}_\text{D} = 35 \text{ A}; \\       V_{sup} \leq 50 \text{ V}; \text{ unclamped};  \text{t}_\text{p} = 100  \mu\text{s}; \\       R_{GS} = 50  \Omega $	-	300	mJ
I <sub>AS</sub>	non-repetitive avalanche current	V <sub>sup</sub> ≤ 50 V; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; R <sub>GS</sub> = 50 Ω; unclamped	-	35	А





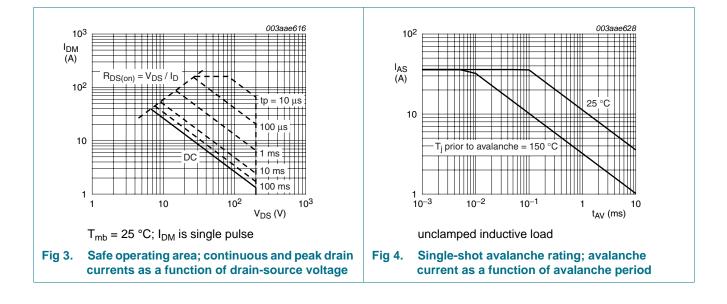


**Product data sheet** 

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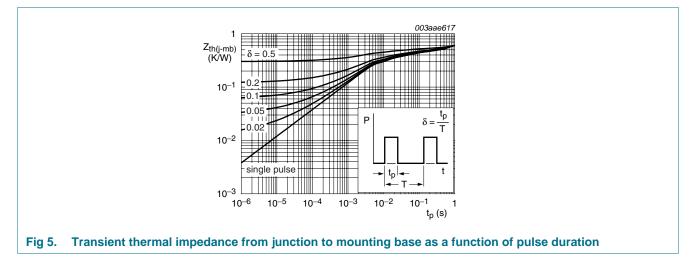
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### 5. Thermal characteristics

Table J.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	-	-	0.6	K/W	
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W



#### Table 5. Thermal characteristics

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### 6. Characteristics

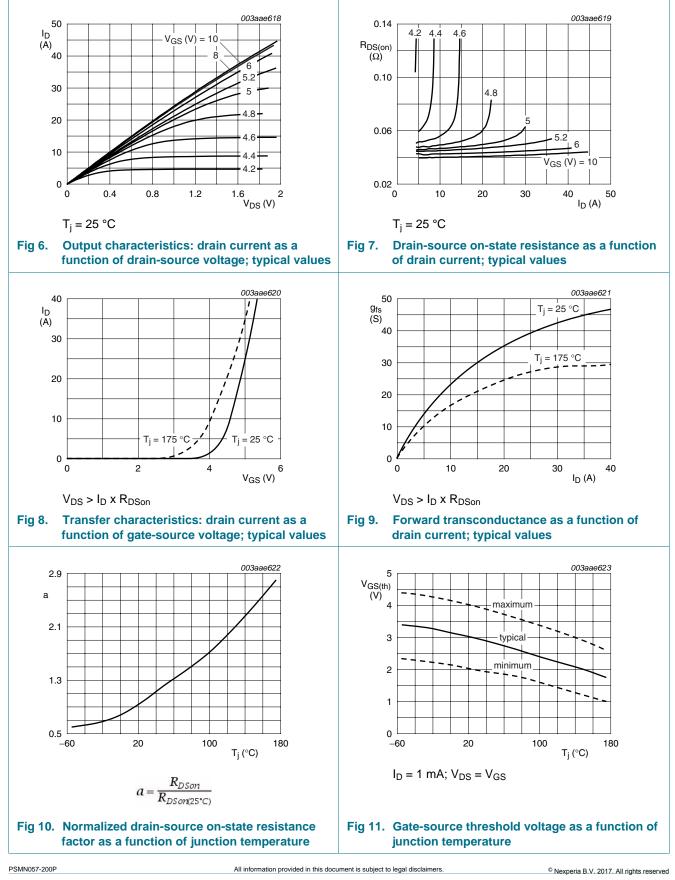
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub> drain-source breakdown voltage		$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	178	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	200	-	-	V
V <sub>GS(th)</sub>	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.03	10	μA
		$V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 10 V; $I_D$ = 17 A; $T_j$ = 175 °C	-	-	165	mΩ
	resistance	$V_{GS}$ = 10 V; $I_D$ = 17 A; $T_j$ = 25 °C	-	41	57	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 39 \text{ A}; V_{DS} = 160 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}$	-	96	-	nC
Q <sub>GS</sub>	gate-source charge		-	13	-	nC
$Q_{GD}$	gate-drain charge		-	37	50	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;$	-	3750	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \ ^{\circ}C$	-	385	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	180	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 100 \text{ V};  \text{R}_{\text{L}} = 2.7  \Omega;  \text{V}_{\text{GS}} = 10 \text{ V}; \\$	-	18	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5.6 \ \Omega; \ T_j = 25 \ ^{\circ}C$	-	58	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	105	-	ns
t <sub>f</sub>	fall time		-	78	-	ns
L <sub>D</sub>	internal drain inductance	measured from drain lead to centre of die ; $T_j = 25 \text{ °C}$	-	4.5	-	nH
		measured from tab to centre of die ; $T_j = 25 ^\circ\text{C}$	-	3.5	-	nH
L <sub>S</sub>	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode	·				
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 20 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	133	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C	-	895	-	nC

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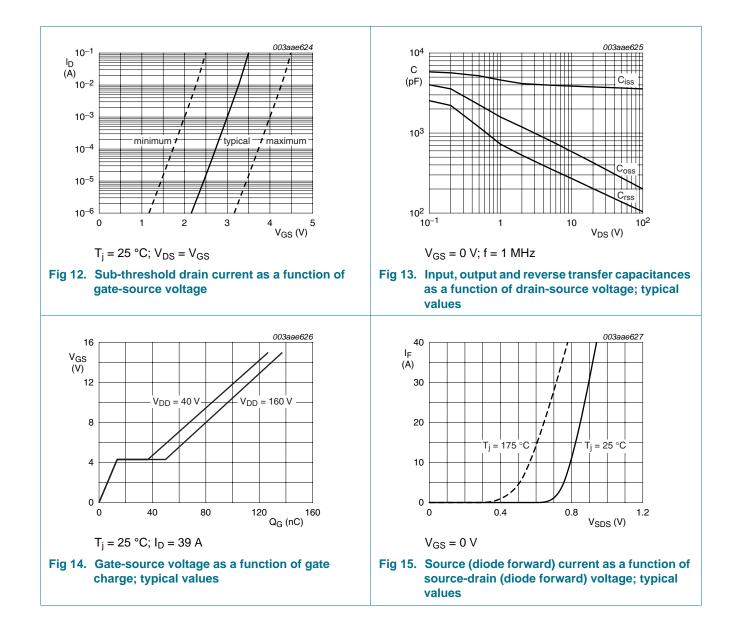
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#### **Package outline** 7.

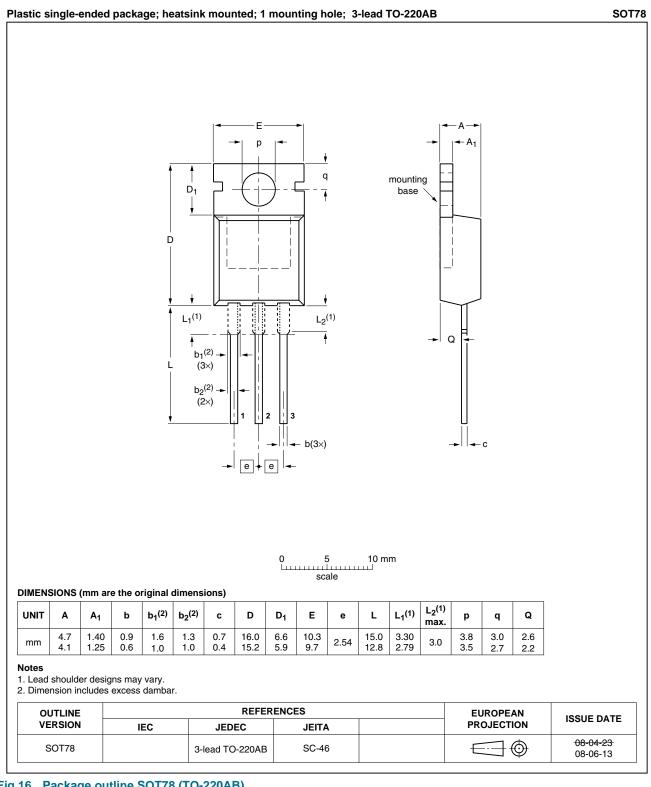


Fig 16. Package outline SOT78 (TO-220AB)

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### 8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN057-200P v.2	20110104	Product data sheet	-	PSMN057-200P v.1
Modifications:	<ul> <li>The format of of NXP Semic</li> </ul>	this data sheet has been rec conductors.	lesigned to comply with	n the new identity guidelines
	<ul> <li>Legal texts had</li> </ul>	we been adapted to the new	company name where	appropriate.
PSMN057-200P v.1	20000601	Product specification	-	-

### 9. Legal information

### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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